54ABT573 Octal D-Type Latch with TRI-STATE Outputs

## National Semiconductor

## 54ABT573 Octal D-Type Latch with TRI-STATE<sup>®</sup> Outputs

#### **General Description**

The 'ABT573 is an octal latch with buffered common Latch Enable (LE) and buffered common Output Enable  $(\overline{\text{OE}})$  inputs.

This device is functionally identical to the 'ABT373 but has different pinouts.

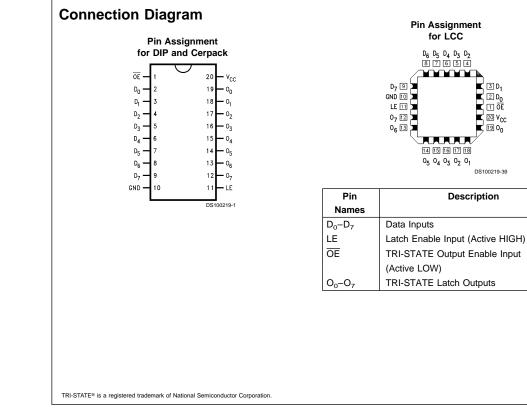
#### Features

- Inputs and outputs on opposite sides of package allow easy interface with microprocessors
- Useful as input or output port for microprocessors

- Functionally identical to 'ABT373
- TRI-STATE outputs for bus interfacing
- Output sink capability of 48 mA, source capability of 24 mA
- Output switching specified for both 50 pF and 250 pF loads
- Guaranteed latchup protection
- High impedance glitch-free bus loading during entire power up and power down
- Nondestructive hot insertion capability
- Standard Microcircuit Drawing (SMD) 5962-9321901

#### **Ordering Code**

Military	Package Package Description Number		
54ABT573J-QML	J20A	20-Lead Ceramic Dual-In-Line	
54ABT573W-QML	W20A	20-Lead Cerpack	
54ABT573E-QML	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C	



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#### **Functional Description**

The 'ABT573 contains eight D-type latches with TRI-STATE output buffers. When the Latch Enable (LE) input is HIGH, data on the  $D_n$  inputs enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable  $(\overline{OE})$ input. When  $\overline{OE}$  is LOW, the buffers are in the bi-state mode. When  $\overline{OE}$  is HIGH the buffers are in the high impedance mode but this does not interfere with entering new data into the latches.

#### Logic Diagram

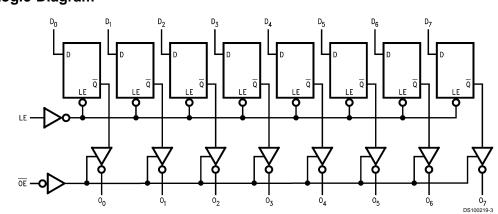
Function Table								
	Outputs							
ŌE	LE	D	0					
L	н	Н	Н					
L	н	L	L					
L	L	Х	0 <sub>0</sub> 7					
н	х	Х	Z					

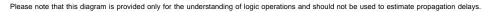
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H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial $O_0 = Value$  stored from previous clock cycle





## Absolute Maximum Ratings (Note 1)

_	
Storage Temperature	–65°C to +150°C
Ambient Temperature under Bias	–55°C to +125°C
Junction Temperature under Bias	
Ceramic	–55°C to +175°C
V <sub>CC</sub> Pin Potential to	
Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Any Output	
in the Disabled or	
Power-Off State	-0.5V to +5.5V
in the HIGH State	–0.5V to V <sub>CC</sub>
Current Applied to Output	
in LOW State (Max)	Twice the rated I <sub>OL</sub> (mA)
DC Latchup Source Current	–500 mA

Over Voltage Latchup (I/O)

# Recommended Operating Conditions

Free Air Ambient Temperature	
Military	–55°C to +125°C
Supply Voltage	
Military	+4.5V to +5.5V
Minimum Input Edge Rate	$(\Delta V / \Delta t)$
Data Input	50 mV/ns
Enable Input	20 mV/ns
<b>Note 1:</b> Absolute maximum ratings are values be damaged or have its useful life impaired. Fu conditions is not implied.	

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

## **DC Electrical Characteristics**

Symbol	Para	Parameter ABT573 Uni		Units	Vcc	Conditions			
			Min	Тур	Max	1			
VIH	Input HIGH Voltage		2.0			V		Recognized HIGH Signal	
V <sub>IL</sub>	Input LOW Voltage				0.8	V		Recognized LOW Signal	
V <sub>CD</sub>	Input Clamp Diode Volt	age			-1.2	V	Min	I <sub>IN</sub> = -18 mA	
V <sub>OH</sub>	Output HIGH Voltage	54ABT	2.5			V	Min	I <sub>OH</sub> = -3 mA	
		54ABT	2.0					I <sub>OH</sub> = -24 mA	
V <sub>OL</sub>	Output LOW Voltage	54ABT			0.55	V	Min	I <sub>OL</sub> = 48 mA	
I <sub>IH</sub>	Input HIGH Current				5	μA	Max	V <sub>IN</sub> = 2.7V (Note 4)	
					5			V <sub>IN</sub> = V <sub>CC</sub>	
I <sub>BVI</sub>	Input HIGH Current				7	μA	Max	V <sub>IN</sub> = 7.0V	
	Breakdown Test								
IIL	Input LOW Current				-5	μA	Max	V <sub>IN</sub> = 0.5V (Note 4)	
					-5			$V_{IN} = 0.0V$	
V <sub>ID</sub>	Input Leakage Test		4.75			V	0.0	I <sub>ID</sub> = 1.9 μA	
								All Other Pins Grounded	
I <sub>OZH</sub>	Output Leakage Curren	t			50	μA	0 – 5.5V	$V_{OUT} = 2.7V; \overline{OE} = 2.0V$	
I <sub>OZL</sub>	Output Leakage Curren	t			-50	μA	0 – 5.5V	$V_{OUT} = 0.5V; \overline{OE} = 2.0V$	
I <sub>OS</sub>	Output Short-Circuit Cu	rrent	-100		-275	mA	Max	V <sub>OUT</sub> = 0.0V	
I <sub>CEX</sub>	Output High Leakage C	urrent			50	μA	Max	V <sub>OUT</sub> = V <sub>CC</sub>	
I <sub>ZZ</sub>	Bus Drainage Test				100	μA	0.0	V <sub>OUT</sub> = 5.5V; All Others GND	
I <sub>CCH</sub>	Power Supply Current				50	μA	Max	All Outputs HIGH	
I <sub>CCL</sub>	Power Supply Current				30	mA	Max	All Outputs LOW	
I <sub>CCZ</sub>	Power Supply Current				50	μA	Max	OE = V <sub>CC</sub>	
								All Others at V <sub>CC</sub> or GND	
I <sub>CCT</sub>	Additional I <sub>CC</sub> /Input	Outputs Enabled			2.5	mA		$V_{I} = V_{CC} - 2.1V$	
		Outputs TRI-STATE			2.5	mA	Max	Enable Input V <sub>I</sub> = V <sub>CC</sub> - 2.1V	
		Outputs TRI-STATE			2.5	mA		Data Input V <sub>I</sub> = V <sub>CC</sub> - 2.1V	
								All Others at $V_{CC}$ or GND	
I <sub>CCD</sub>	Dynamic I <sub>CC</sub>	No Load				mA/	Max	Outputs Open	
	(Note 4)				0.12	MHz		$\overline{OE}$ = GND, LE = V <sub>CC</sub> (Note 3)	
								One Bit Toggling, 50% Duty Cycle	

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Note 3: For 8 bits toggling,  $I_{\rm CCD}$  < 0.8 mA/MHz.

Note 4: Guaranteed but not tested.

10V

DC	<b>Electrical</b>	Characteristics
		Characteristics

Symbol	Parameter	Min	Max	Units	V <sub>cc</sub>	Conditions
						$C_{L}$ = 50 pF, $R_{L}$ = 500 $\Omega$
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>		0.9	V	5.0	$T_A = 25^{\circ}C$ (Note 5)
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>		-1.7	V	5.0	$T_A = 25^{\circ}C$ (Note 5)

Note 5: Max number of outputs defined as (n). n – 1 data inputs are driven 0V to 3V. One output at LOW. Guaranteed, but not tested.

### **AC Electrical Characteristics**

Symbol	Parameter	54ABT T <sub>A</sub> = -55°C to +125°C		Units	Fig. No.	
	Γ					
		$V_{\rm CC} = 4.5$	iV to 5.5V			
		C <sub>L</sub> =	50 pF			
	Γ	Min	Max			
t <sub>PLH</sub>	Propagation Delay	1.0	6.4	ns	Figure 4	
t <sub>PHL</sub>	D <sub>n</sub> to O <sub>n</sub>	1.5	6.7			
t <sub>PLH</sub>	Propagation Delay	1.0	7.1	ns	Figure 4	
t <sub>PHL</sub>	LE to O <sub>n</sub>	1.5	7.5			
t <sub>PZH</sub>	Output Enable Time	0.8	6.5	ns	Figure 6	
t <sub>PZL</sub>		1.5	7.2			
t <sub>PHZ</sub>	Output Disable Time	1.5	7.7	ns	Figure 6	
t <sub>PLZ</sub>	Time	1.0	7.0			

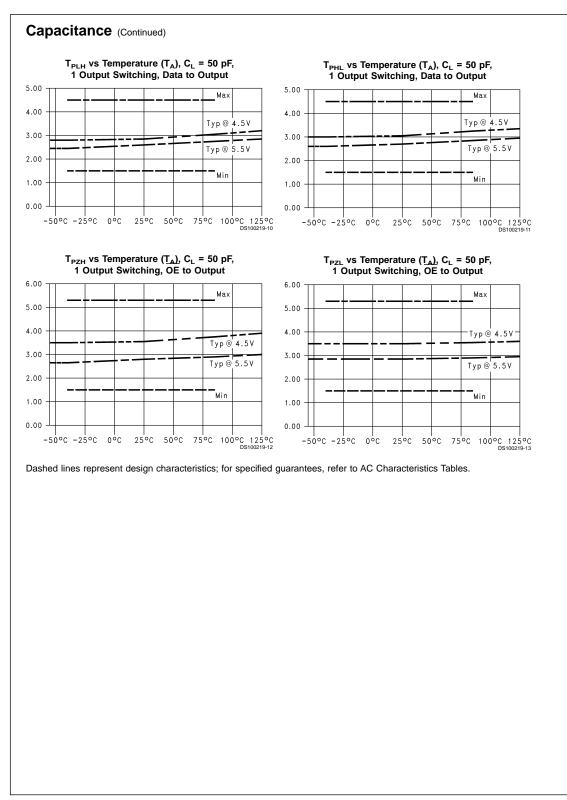
## **AC Operating Requirements**

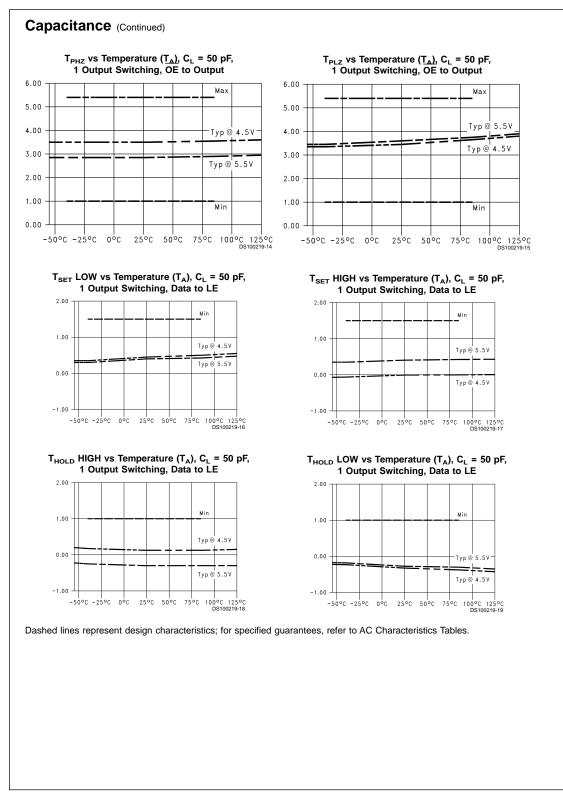
Symbol	Parameter	$\frac{54ABT}{T_{A} = -55^{\circ}C \text{ to } +125^{\circ}C}$ $V_{CC} = 4.5V \text{ to } 5.5V$ $C_{L} = 50 \text{ pF}$		Units	Fig. No.
		Min	Max		
t <sub>s</sub> (H)	Set Time, HIGH	2.5		ns	Figure 7
t <sub>s</sub> (L)	or LOW D <sub>n</sub> to LE	2.5			
t <sub>h</sub> (H)	Hold Time, HIGH	2.5		ns	Figure 7
t <sub>h</sub> (L)	or LOW D <sub>n</sub> to LE	2.5			
t <sub>w</sub> (H)	Pulse Width,	3.3		ns	Figure 5
	LE HIGH				

## Capacitance

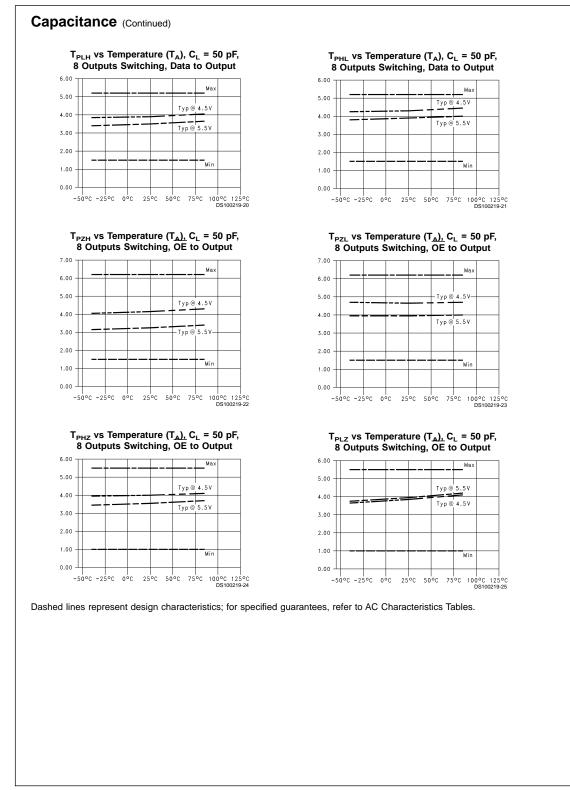
Symbol	Parameter	Тур	Units	Conditions		
				(T <sub>A</sub> = 25°C)		
C <sub>IN</sub>	Input Capacitance	5	pF	$V_{CC} = 0V$		
C <sub>OUT</sub> (Note 6)	Output Capacitance	9	pF	$V_{CC} = 5.0V$		
Note C. C. is measured at fragmany ( A Mile and Mile OTD 000D Mathed 0040						

Note 6:  $C_{OUT}$  is measured at frequency f = 1 MHz per MIL-STD-883B, Method 3012.

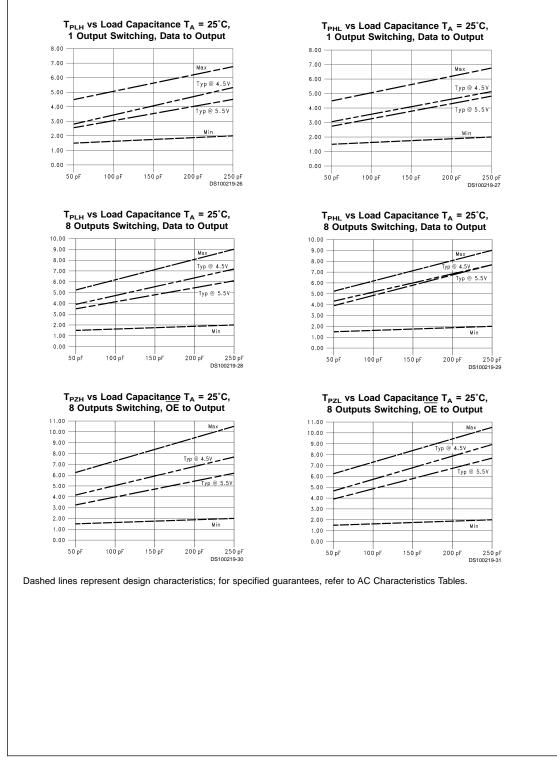


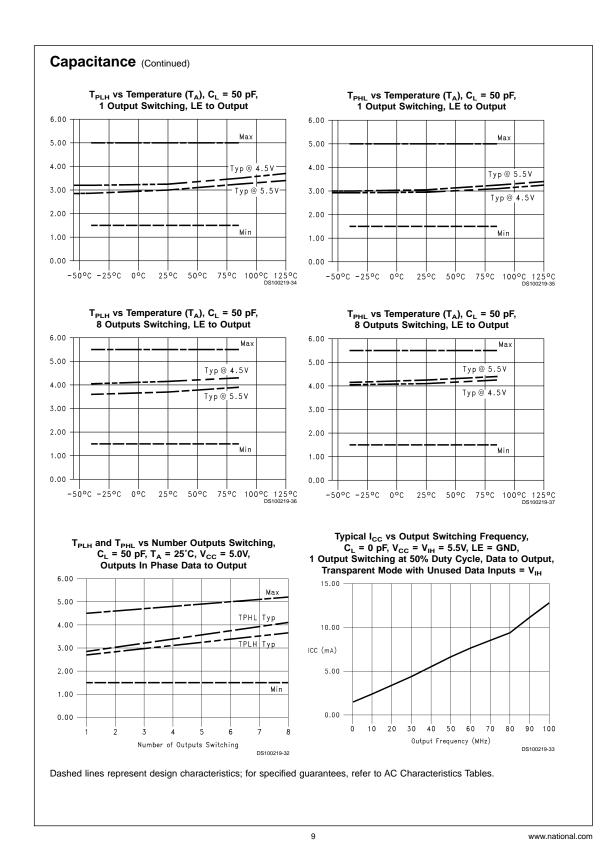


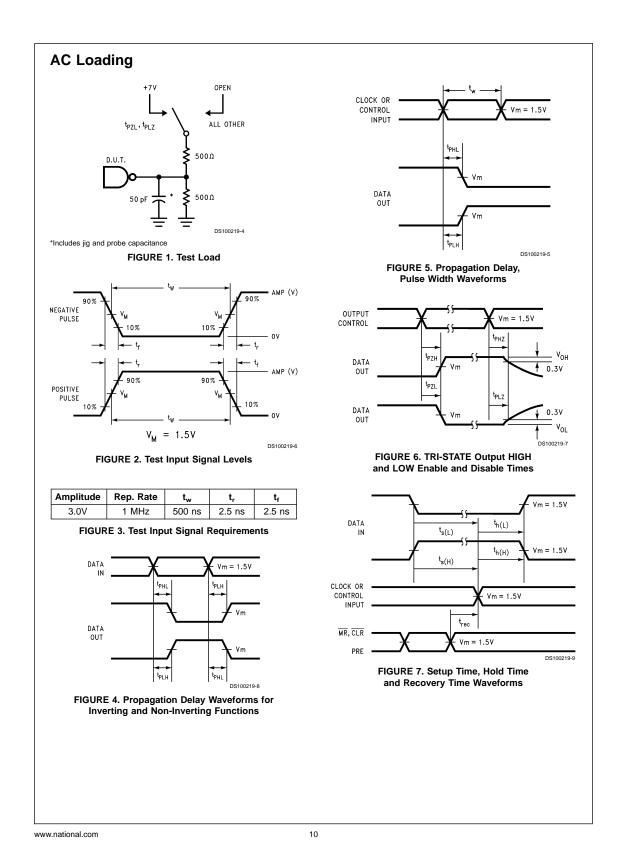
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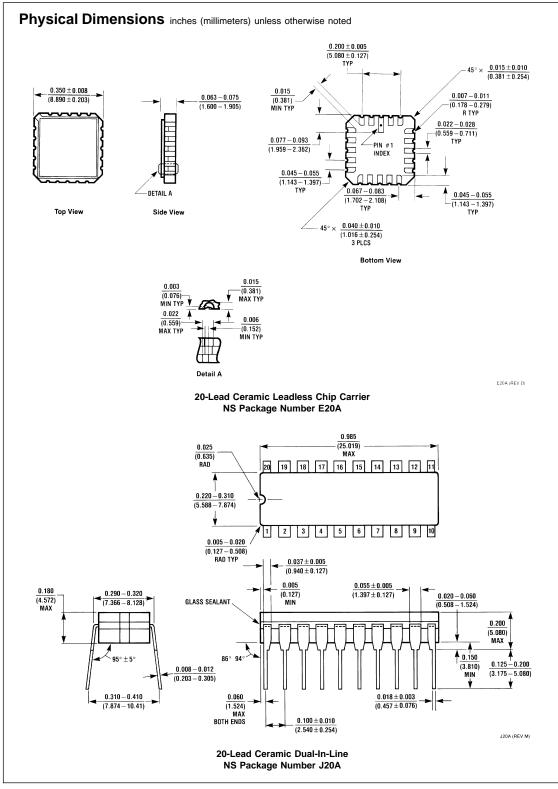


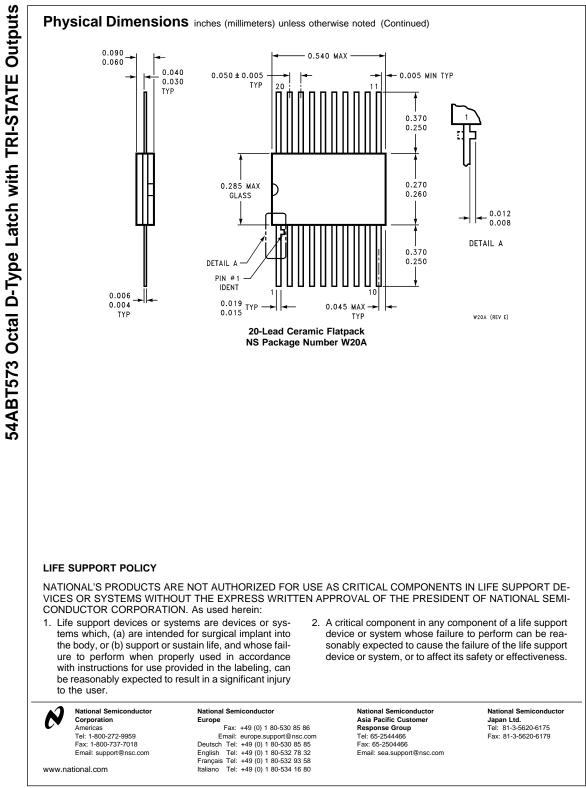






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